

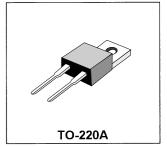
Ultra Fast Recovery Rectifier Diodes

... Designed for use in switching power supplies. inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

- * High Surge Capacity
- * Low Power Loss, High efficiency
- * Glass Passivated chip junctions
- * 150 °C Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction
- * Low Forward Voltage, High Current Capability
- * High-Switching Speed 50 & 75 Nanosecond Recovery Time
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O

ULTRA FAST RECTIFIERS

8 AMPERES 700 -- 1000 VOLTS

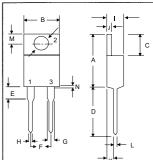


MAXIMUM RATINGS

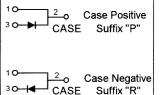
Characteristic	Symbol	U08A				Unit
		70	80	90	100	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	700	800	900	1000	V
RMS Reverse Voltage	V _{R(RMS)}	490	560	630	700	٧
Average Rectifier Forward Current	 F(AV)	8.0			Α	
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware,single phase,60Hz)	FSM	125			A	
Operating and Storage Junction Temperature Range	T _j , T _{stg}	- 65 to + 150			°C	

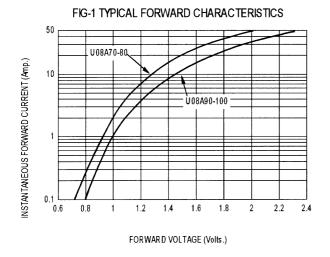
ELECTRICAL CHARACTERISTICS

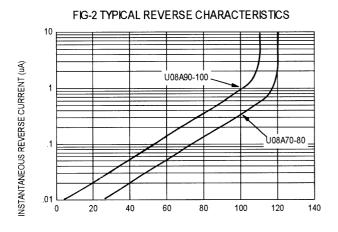
Characteristic	Symbol		Unit		
		70	80	90	100
Maximum Instantaneous Forward Voltage (I_F =8.0 Amp, T_C = 25 $^{\circ}$ C) (I_F =8.0 Amp, T_C = 100 $^{\circ}$ C)	V _F	1.75 1.65			V
Maximum Instantaneous Reverse Current (Rated DC Voltage, T _c = 25 °C) (Rated DC Voltage, T _c = 100 °C)	I _R	10 500			uA
Reverse Recovery Time (I _F = 0.5 A, I _R =1.0 A, I _{rr} =0.25 A)	T _{rr} 50 75		75	ns	
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	C _P	40			pF

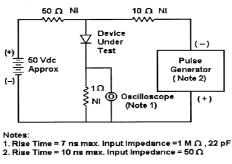


	MILLMETERS			
DIM	MIN	MAX		
Α	14.68	15.32		
В	9.78	10.42		
С	6.01	6.52		
D	13.06	14.62		
Ε	3.57	4.07		
F	4.83	5.33		
G	1.12	1.36		
Н	0.72	0.96		
1	4.22	4.98		
J	1.14	1.36		
K	2.20	2.97		
L	0.33	0.55		
M	2.48	2.98		
N		1.00		
0	3.70	3.90		

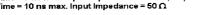


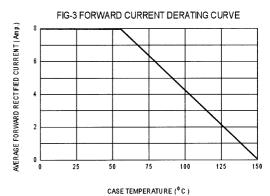


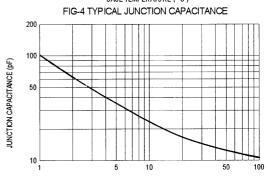


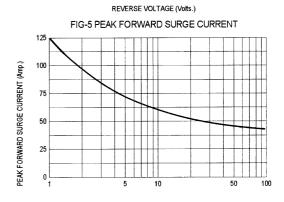


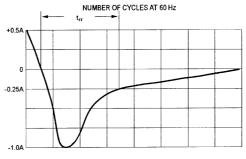
PERCENT OF PEAK REVERSE VOLTAGE(%)











Set time base for 10/20 ns/div

Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram



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